

Claims

sub B12
1. "amended". Transistor comprising elements of a bipolar static induction transistor: a gate, a source and a channel -- on each of (the) sides of a lightly doped substrate.

2. "canceled".

926
3. "amended". Transistor according to claim 1 in which (comprising) on each of (the) sides of (a) said lightly doped substrate with the impurity concentration of about 10.sup.14 cm.sup.-3 an epitaxial layer of the same type of conductivity with the impurity concentration of about 10.sup.17 cm.sup.-3, in which said elements of (a) said bipolar static induction transistor: (a) said gate, (a) said source and (a) said channel -- are disposed.

4. "amended". Transistor according to claims 1 or 3 (differing) in (that) which one of (the) channels of multielement structures on each of sides of (the) said substrate is thicker than other channels, (and this) said channel is connected to a separate electrode.

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